N Channel Power MOSFET



Rev. V2

Features

- Available in JAN, JANTX, JANTXV and JANS per MIL-PRF-19500/547
- Features Low On-Resistance, Fast Switching Speed and Low Threshold
- Low Input Capacitance
- Ideal for Hi-Rel Solid-State Relays, Battery Operated Systems and Driver Applications for Relays, Solenoids, Lamps, Displays, Memories, etc.
- TO-39 (TO-205AD) and Surface Mount UB Package Types

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Drain-Source Breakdown Voltage	V_{DS} = 0, I _G = 1.0 µA dc 2N6660, UB V _{DS} = 0, I _G = 1.0 µA dc 2N6661, UB	V _{DS}	V dc	60 90	
Gate-Source Threshold Voltage	V_{DS} = V_{GS} , I_D = 1 mA dc	$V_{GS(th)}$	V dc	0.8	2.0
Gate Current	V _{DS} = 0, V _{GS} = <u>+</u> 20V	I _{GSS}	nA dc	—	<u>+</u> 100
Zero Gate Voltage Drain Current	V_{GS} = 0 V, V_{DS} = 48 V dc 2N6660, UB V _{GS} = 0 V, V_{DS} = 72 V dc 2N6661, UB	I _{DSS}	µA dc		1.0
Drain-Source On-State Resistance	V_{GS} = 10 V dc, I _D = 1.0 A dc 2N6660, UB V _{GS} = 10 V dc, I _D = 1.0 A dc 2N6661, UB	r _{DS(on)} 1	Ω		3.0 4.0
Drain-Source On-State Resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 5V, \ I_{D} = 0.3A & 2N6660, \ UB \\ V_{GS} = 5V, \ I_{D} = 0.3A & 2N6661, \ UB \end{array}$	$r_{\text{DS(on)}}^2$	Ω	_	5.0 5.3
Forward Transconductance	V_{DS} = V_{GS} = 7.5V, I_{D1} = 525 mA dc2N6660, UB V_{DS} = V_{GS} = 7.5V, I_{D2} = 475 mA dc 2N6661, UB	g fs	mS	170	_
Diode Forward Voltage	$I_{S} = 0.99 \text{ A}, V_{GS} = 0 \text{ V} 2N6660, UB$ $I_{S} = 0.86 \text{ A}, V_{GS} = 0 \text{ V} 2N6661, UB$	V_{SD}	V (pk)	0.7 0.7	1.6 1.4

N Channel Power MOSFET



ns

t_{d(off)}

10

Rev. V2

Electrical Characteristics

Parameter	Test Conditions	Symbol	Units	Min.	Max.	
Dynamic Characteristics				I		
Static, Drain-Source On State Resistance	V _{GS} = 10 V dc; I _D = 1.0 A dc; T _C = +125°C 2N6660, UB 2N6661, UB	r _{DS(on)3}	Ω	_	5.6 7.5	
Drain Current	T_{C} = +125°C; V_{GS} = 0 V V_{DS} = 48 V 2N6660, UB V_{DS} = 72 V 2N6661, UB	I _{DSS2}	μΑ	_	100	
Small-Signal, Common-Source Short Circuit Reverse Transfer Capacitance	V_{DS} = 25 V dc, V_{GS} = 0 V; f = 1MHz	C _{rss}	pF	_	10	
Small-Signal, Common-Source Short Circuit Input Capacitance	V_{DS} = 25 V dc; V_{GS} = 0 V; f = 1.0 MHz	C _{iss}	pF	_	50	
Small-Signal, Common-Source Short Circuit Output Capacitance	V_{DS} = 25 V dc; V_{GS} = 0 V; f = 1.0 MHz	C _{oss}	pF		40	
Parameter	Test Conditions	Symbol	Units	Min.	Max.	
Switching Characteristics						
Turn-On Delay Time	$R_{GS} = 23\Omega, R_L = 23\Omega, V_{GEN} = 10 V$ $V_{DD} = 25 V dc; I_D = 1 A dc$	t _{d(on)}	ns	_	10	
Turn Off Dolay Time	R _{GS} = 23Ω, R _L = 23Ω, V _{GEN} = 10 V	+	ne		10	

VPT Components and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice. Visit www.vptcomponents.com for additional data sheets and product information.

 V_{DD} = 25 V dc; I_D = 1 A dc

Turn-Off Delay Time



N Channel Power MOSFET

Rev. V2

Absolute Maximum Ratings ($T_A = +25^{\circ}C$ unless otherwise noted)

Ratings	Symbol	Value
Gate-Source Voltage	V _{GS}	<u>+</u> 20 V dc
Drain-Source Voltage	V _{DS}	2N6660, UB 60 V dc 2N6661, UB 90 V dc
Drain-Gate Voltage	V _{DGR}	2N6660, UB 60 V dc 2N6661, UB 90 V dc
Continuous Drain-Current	I _{D1} ⁽³⁾	2N6660, UB 0.99 A dc 2N6661, UB 0.86 A dc
Continuous Drain-Current T _C = +100°C	I _{D2} ⁽³⁾	2N6660, UB 0.62 A dc 2N6661, UB 0.54 A dc
Source Current	I _S	2N6660, UB -0.99 A dc 2N6661, UB -0.86 A dc
Peak Drain Current	I _{DM}	3 A (pk)
Maximum Power Dissipation (TO-39) @ $T_c= 25^{\circ}C^{(1)}$ @ $T_A = 25^{\circ}C$	P _T	6.25 W 725 mW
Maximum Power Dissipation (UB) @ T _C = 25°C ⁽¹⁾ @ T _A = 25°C	PT	2.5 W 570 mW
Junction & Storage Temperature Range	$T_{Jand}T_{STG}$	-65°C to +150°C
Thermal Resistance, Junction to Case Thermal Resistance, Junction to Case (UB)	R₀JC	20°C/W 40°C/W

$$I_{D} = \sqrt{\frac{T_{JM} - T_{C}}{\left(R_{\theta JC}\right) x \left(R_{DS}(on) at T_{JM}\right)}}$$

VPT Components and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice. Visit <u>www.vptcomponents.com</u> for additional data sheets and product information.

N Channel Power MOSFET



Rev. V2

Outline Drawing TO-205AD (TO-39)



FIGURE 1. Physical dimensions (TO-205AD).

VPT Components and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice. Visit <u>www.vptcomponents.com</u> for additional data sheets and product information.

N Channel Power MOSFET

Outline Drawing TO-205AD (TO-39)

Ltr Dimensions Notes Inches Millimeters Min Max Min Max 7.75 CD 305 .335 8.51 CH 240 260 6.10 6.60 HD 335 8.51 .370 9.40 2 TW .028 .034 0.71 0.86 3 TL 029 .045 0.74 1.14 0.53 LD .016 .021 0.41 7,8 LL 500 .750 12.70 19.05 7,8 LC 0.200 TP 5.08 TP 6 LU .016 .019 0.41 0.48 7,8 .050 L₁ 1.27 7,8 250 6.35 7,8 L2 Ρ 100 2.545 .050 1.27 4 Q 9 R .010 0.25 45° TP 45° TP 6 α

MIL-PRF-19500/547D

NOTES:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- 2. Beyond radius (r) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- 3. Dimension TL measured from maximum HD.
- 4. Outline in this zone is not controlled.
- 5. Dimension CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 +.001, -.000 inch (1.37 +0.03, -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- LU applies between L₁ and L₂. LD applies between L₂ and L minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
- All three leads.
- 9. Radius (r) applies to both inside corners of tab.
- 10. Drain is electrically connected to the case.

FIGURE 1. Physical dimensions(TO-205AD) - Continued.

5



Rev. V2

VPT Components and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice. Visit <u>www.vptcomponents.com</u> for additional data sheets and product information.

N Channel Power MOSFET

Outline Drawing (UB)



FIGURE 2. Physical dimensions for UB and UBC style surface mount package.

BH

CL

CW

LL1

NOTES: 1.

2.

only).

Three places.

7. For design reference only.

.055

.022

.069

.128

.108

.038

1.02

1.40

0.56

Hatched areas on package denote metallized areas.

4. Dimension BH for UB packages with medal lid. 5. Dimension BH for UBC packages with ceramic lid.

1.42

1.75

3.25

2.74

0.97

5

6

Dimensions are in inches. Millimeters are given for general information only.

In accordance with ASME Y14.5M, diameters are equivalent to Øx symbology.

LW

r

r1

r2

3. Pad 1 = Gate, 2 = Source, 3 = Drain, 4 = shielding connected to the lid (UB only) or lid braze ring (UBC

.016

.024

.008

.012

.022

0.41

0.61

0.20

0.30

0.56

6

7

6

BL LW SPLS SPLS LS2 LS2 CERAMIC LL2 LS2 METALLIZATION											
	Dimensions							Dime	nsions		
Symbol	Inc	hes	Millimeters		Natas	Symbol	Inches		inches Millimeters		Notor
	Min	Max	Min	Max	notes	-,	Min	Max	Min	Max	notes
BL	.115	.128	2.92	3.25		LL2	.009	.036	0.23	0.89	6
BW	.085	.108	2.16	2.74		LS1	.035	.040	0.89	1.02	
BH	.040	.056	1.02	1.42	4	LS2	.071	.079	1.80	2.01	







Rev. V2

N Channel Power MOSFET



Rev. V2

Graphs



FIGURE 2. Maximum safe operating area.

VPT Components and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice. Visit <u>www.vptcomponents.com</u> for additional data sheets and product information.

N Channel Power MOSFET



Rev. V2

Graphs



ACTIVE REGION

FIGURE 2. Maximum safe operating area - Continued.

VPT Components and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice. Visit <u>www.vptcomponents.com</u> for additional data sheets and product information.

N Channel Power MOSFET



VPT COMPONENTS. ALL RIGHTS RESERVED.

Information in this document is provided in connection with VPT Components products. These materials are provided by VPT Components as a service to its customers and may be used for informational purposes only. Except as provided in VPT Components Terms and Conditions of Sale for such products or in any separate agreement related to this document, VPT Components assumes no liability whatsoever. VPT Components assumes no responsibility for errors or omissions in these materials. VPT Components may make changes to specifications and product descriptions at any time, without notice. VPT Components makes no commitment to update the information and shall have no responsibility whatsoever for conflicts or incompatibilities arising from future changes to its specifications and product descriptions. No license, express or implied, by estoppels or otherwise, to any intellectual property rights is granted by this document.

THESE MATERIALS ARE PROVIDED "AS IS" WITHOUT WARRANTY OF ANY KIND, EITHER EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF VPT COMPONENTS PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, CONSEQUENTIAL OR INCI-DENTAL DAMAGES, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT. VPT COMPONENTS FURTHER DOES NOT WARRANT THE ACCURA-CY OR COMPLETENESS OF THE INFORMATION, TEXT, GRAPHICS OR OTHER ITEMS CON-TAINED WITHIN THESE MATERIALS. VPT COMPONENTS SHALL NOT BE LIABLE FOR ANY SPECIAL, IN-DIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES, INCLUDING WITHOUT LIMITATION, LOST REVE-NUES OR LOST PROFITS, WHICH MAY RESULT FROM THE USE OF THESE MATERIALS.

VPT Components products are not intended for use in medical, lifesaving or life sustaining applications. VPT Components customers using or selling VPT Components products for use in such applications do so at their own risk and agree to fully indemnify VPT Components for any damages resulting from such improper use or sale.

VPT Components and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice. Visit <u>www.vptcomponents.com</u> for additional data sheets and product information.